

## Product Summary

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> max     | I <sub>D</sub><br>T <sub>C</sub> = +25°C<br>(Note 9) |
|-------------------|-----------------------------|--|
| 60V               | 8mΩ @ V <sub>GS</sub> = 10V | 100A   |

## Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

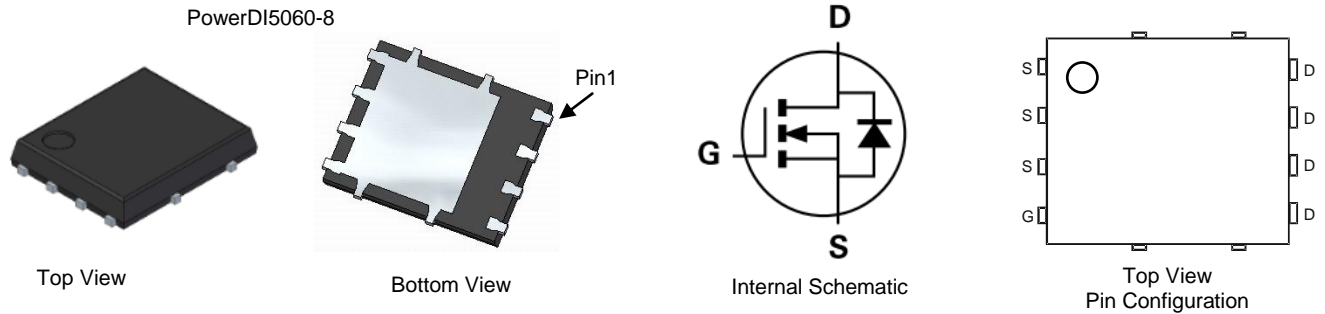
## Description and Applications

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R<sub>DS(ON)</sub> and yet maintain superior switching performance.

- Motors, Lamps and Solenoid Control
- Transmission Control
- Ultra High Performance Power Switching

## Mechanical Data

- Case: PowerDI<sup>®</sup> 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208
- Weight: 0.097 grams (Approximate)

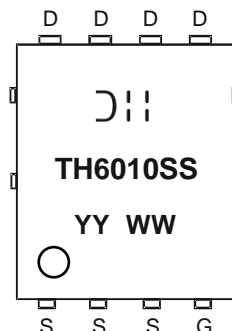


## Ordering Information (Note 4)

| Part Number    | Case          | Packaging           |
|----------------|---------------|---------------------|
| DMTH6010SPS-13 | PowerDI5060-8 | 2,500 / Tape & Reel |

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



= Manufacturer's Marking  
 TH6010SS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 19 = 2019)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   | Symbol           | Value                   | Unit |
|--|------------------|-------------------------|------|
| Drain-Source Voltage   | V <sub>DSS</sub> | 60                      | V    |
| Gate-Source Voltage  | V <sub>GSS</sub> | ±20                     | V    |
| Continuous Drain Current (Note 5)  | I <sub>D</sub>   | T <sub>A</sub> = +25°C  | 13.5 |
|  |                  | T <sub>A</sub> = +70°C  | 10.4 |
| Continuous Drain Current (Notes 6 & 9)                                     | I <sub>D</sub>   | T <sub>C</sub> = +25°C  | 100  |
|  |                  | T <sub>C</sub> = +100°C | 75   |
| Maximum Continuous Body Diode Forward Current (Note 6)                     | I <sub>S</sub>   | 100                     | A    |
| Pulsed Continuous Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%) | I <sub>SM</sub>  | 400                     | A    |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)                         | I <sub>DM</sub>  | 400                     | A    |
| Avalanche Current, L = 0.1mH   | I <sub>AS</sub>  | 20                      | A    |
| Avalanche Energy, L = 0.1mH  | E <sub>AS</sub>  | 20                      | mJ   |

**Thermal Characteristics**

| Characteristic                                   | Symbol                            | Value       | Unit |
|--|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)                 | P <sub>D</sub>                    | 2.6         | W    |
| Thermal Resistance, Junction to Ambient (Note 5) | R <sub>θJA</sub>                  | 57          | °C/W |
| Total Power Dissipation (Note 6)                 | P <sub>D</sub>                    | 167         | W    |
| Thermal Resistance, Junction to Case (Note 6)    | R <sub>θJC</sub>                  | 1.1         | °C/W |
| Operating and Storage Temperature Range          | T <sub>J</sub> , T <sub>STG</sub> | -55 to +175 | °C   |

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                          | Symbol              | Min | Typ  | Max  | Unit | Test Condition  |
|---|---------------------|-----|------|------|------|---|
| <b>OFF CHARACTERISTICS (Note 7)</b>     |                     |     |      |      |      |   |
| Drain-Source Breakdown Voltage          | BV <sub>DSS</sub>   | 60  | —    | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA  |
| Zero Gate Voltage Drain Current         | I <sub>DSS</sub>    | —   | —    | 1    | µA   | V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V   |
| Gate-Source Leakage                     | I <sub>GSS</sub>    | —   | —    | ±100 | nA   | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V  |
| <b>ON CHARACTERISTICS (Note 7)</b>      |                     |     |      |      |      |   |
| Gate Threshold Voltage                  | V <sub>GS(TH)</sub> | 2   | —    | 4    | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA                              |
| Static Drain-Source On-Resistance       | R <sub>DS(ON)</sub> | —   | 6.3  | 8    | mΩ   | V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A   |
| Diode Forward Voltage                   | V <sub>SD</sub>     | —   | 0.9  | 1.2  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A  |
| <b>DYNAMIC CHARACTERISTICS (Note 8)</b> |                     |     |      |      |      |   |
| Input Capacitance                       | C <sub>iss</sub>    | —   | 2841 | —    | pF   | V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz                                   |
| Output Capacitance                      | C <sub>oss</sub>    | —   | 690  | —    |      |   |
| Reverse Transfer Capacitance            | C <sub>rss</sub>    | —   | 46   | —    |      |   |
| Gate Resistance                         | R <sub>g</sub>      | —   | 0.55 | —    | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz                                    |
| Total Gate Charge                       | Q <sub>g</sub>      | —   | 38.1 | —    | nC   | V <sub>DS</sub> = 30V, I <sub>D</sub> = 20A, V <sub>GS</sub> = 10V                      |
| Gate-Source Charge                      | Q <sub>gs</sub>     | —   | 8.3  | —    |      |   |
| Gate-Drain Charge                       | Q <sub>gd</sub>     | —   | 9.3  | —    |      |   |
| Turn-On Delay Time                      | t <sub>D(ON)</sub>  | —   | 8.6  | —    | ns   | V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A, R <sub>G</sub> = 3Ω |
| Turn-On Rise Time                       | t <sub>R</sub>      | —   | 8.2  | —    |      |   |
| Turn-Off Delay Time                     | t <sub>D(OFF)</sub> | —   | 17.4 | —    |      |   |
| Turn-Off Fall Time                      | t <sub>F</sub>      | —   | 5.7  | —    |      |   |
| Body Diode Reverse Recovery Time        | t <sub>RR</sub>     | —   | 33.8 | —    | ns   | I <sub>F</sub> = 20A, di/dt = 100A/µs   |
| Body Diode Reverse Recovery Charge      | Q <sub>RR</sub>     | —   | 35.6 | —    | nC   |   |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.
  - Limited by package.

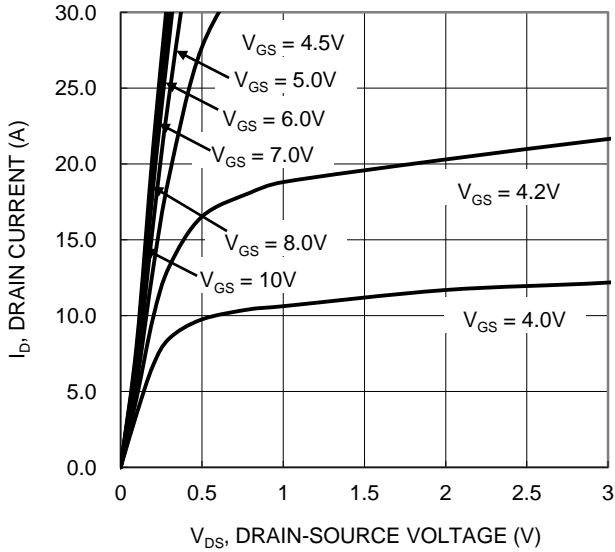


Figure 1. Typical Output Characteristic

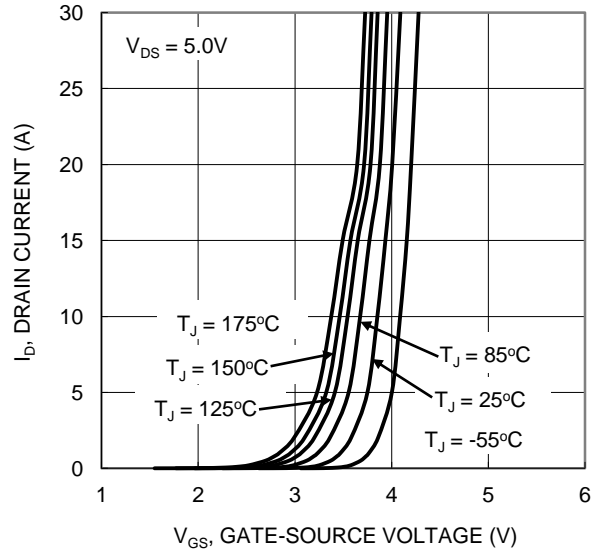


Figure 2. Typical Transfer Characteristic

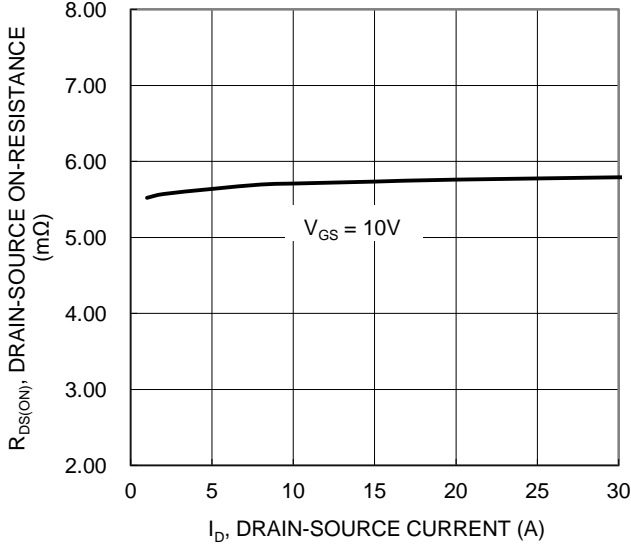


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

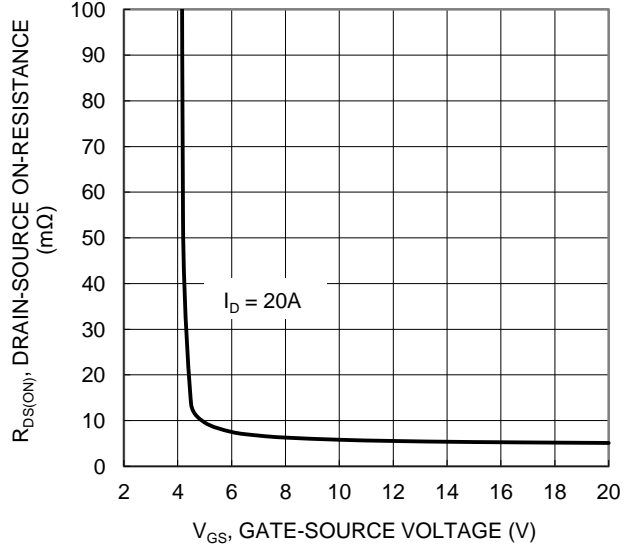


Figure 4. Typical Transfer Characteristic

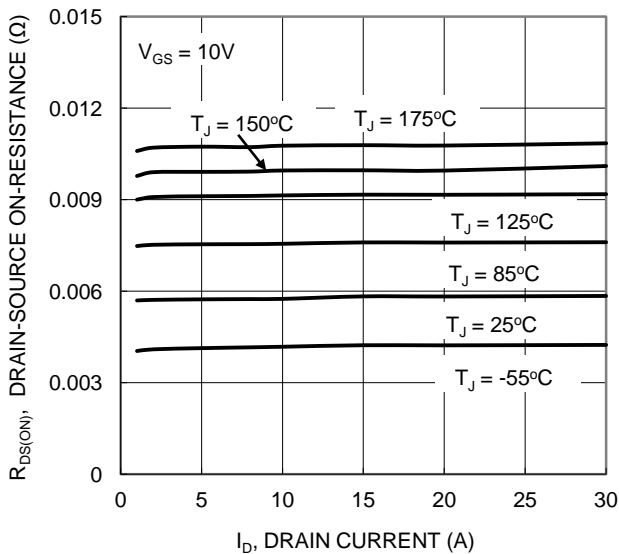


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

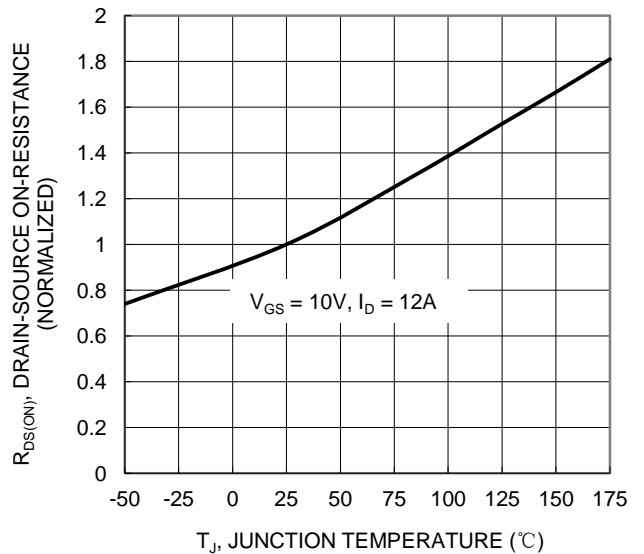


Figure 6. On-Resistance Variation with Temperature

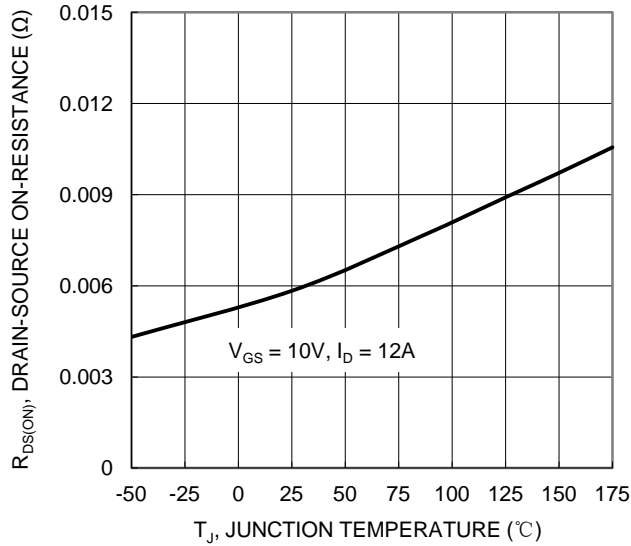


Figure 7. On-Resistance Variation with Temperature

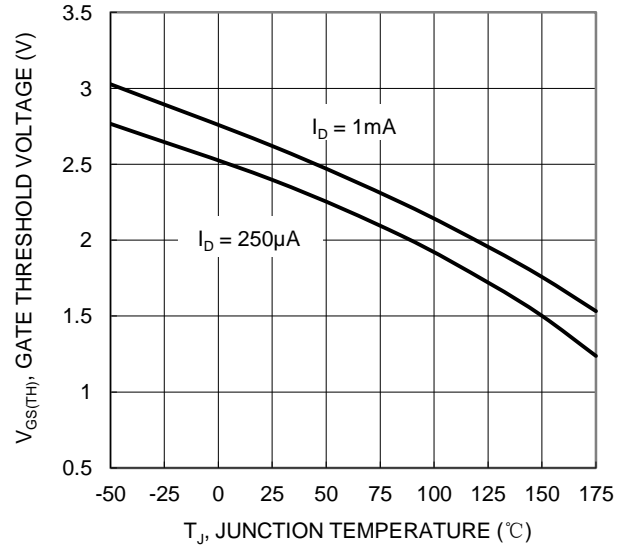


Figure 8. Gate Threshold Variation vs. Temperature

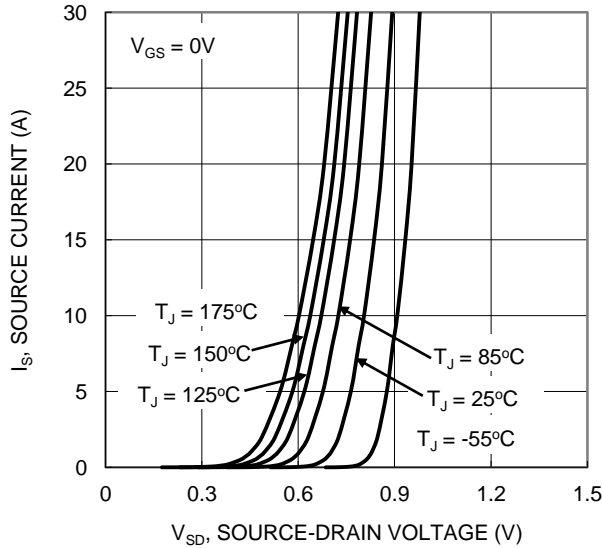


Figure 9. Diode Forward Voltage vs. Current

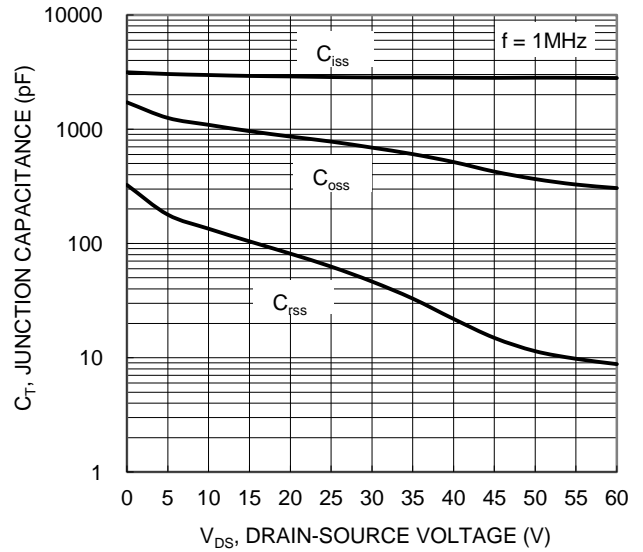


Figure 10. Typical Junction Capacitance

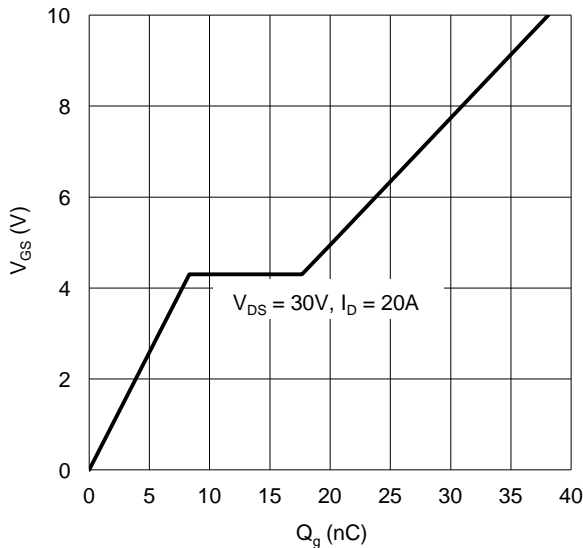


Figure 11. Gate Charge

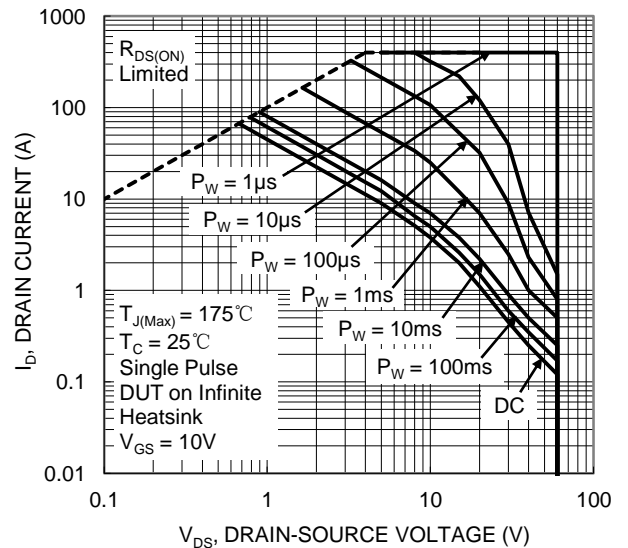


Figure 12. SOA, Safe Operation Area

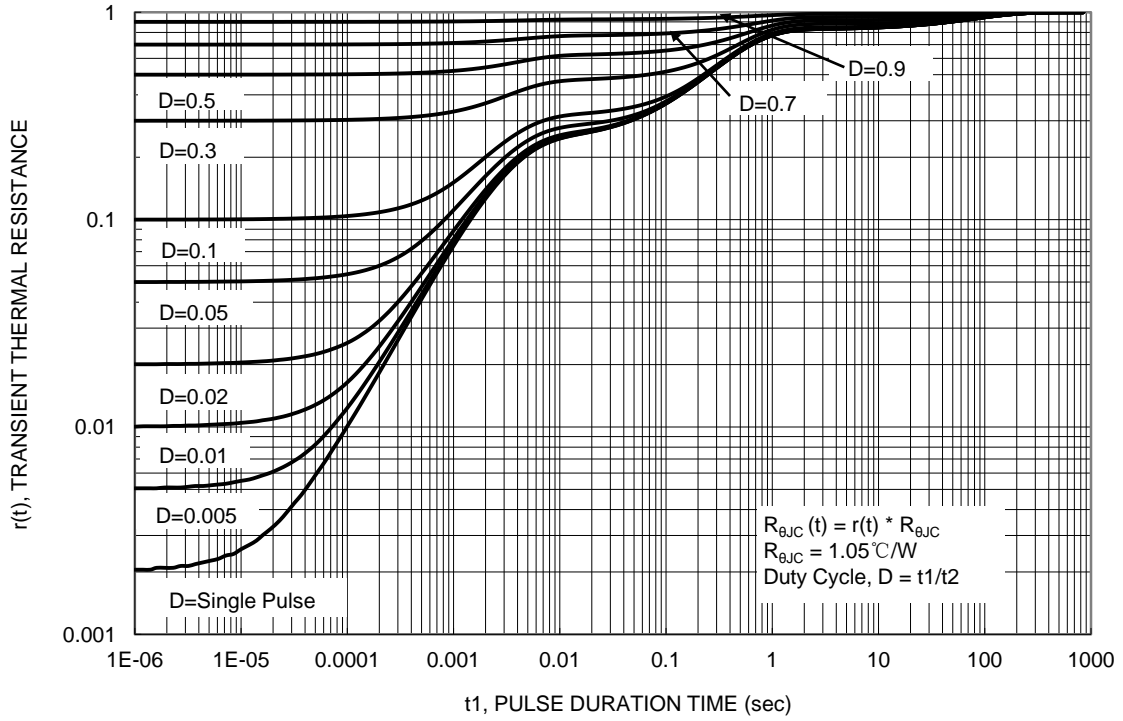
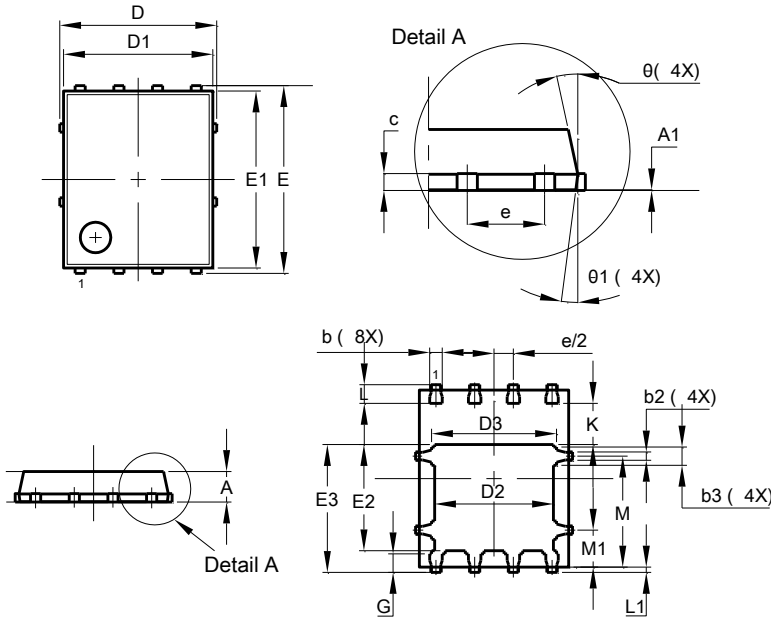


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8**

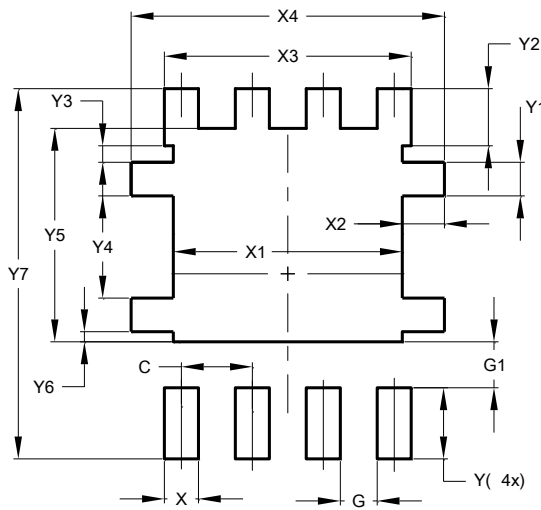


| PowerDI5060-8        |          |       |       |
|----------------------|----------|-------|-------|
| Dim                  | Min      | Max   | Typ   |
| A                    | 0.90     | 1.10  | 1.00  |
| A1                   | 0.00     | 0.05  | -     |
| b                    | 0.33     | 0.51  | 0.41  |
| b2                   | 0.200    | 0.350 | 0.273 |
| b3                   | 0.40     | 0.80  | 0.60  |
| c                    | 0.230    | 0.330 | 0.277 |
| D                    | 5.15 BSC |       |       |
| D1                   | 4.70     | 5.10  | 4.90  |
| D2                   | 3.70     | 4.10  | 3.90  |
| D3                   | 3.90     | 4.30  | 4.10  |
| E                    | 6.15 BSC |       |       |
| E1                   | 5.60     | 6.00  | 5.80  |
| E2                   | 3.28     | 3.68  | 3.48  |
| E3                   | 3.99     | 4.39  | 4.19  |
| e                    | 1.27 BSC |       |       |
| G                    | 0.51     | 0.71  | 0.61  |
| K                    | 0.51     | -     | -     |
| L                    | 0.51     | 0.71  | 0.61  |
| L1                   | 0.100    | 0.200 | 0.175 |
| M                    | 3.235    | 4.035 | 3.635 |
| M1                   | 1.00     | 1.40  | 1.21  |
| $\theta$             | 10°      | 12°   | 11°   |
| $\theta 1$           | 6°       | 8°    | 7°    |
| All Dimensions in mm |          |       |       |

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8**



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 1.270         |
| G          | 0.660         |
| G1         | 0.820         |
| X          | 0.610         |
| X1         | 4.100         |
| X2         | 0.755         |
| X3         | 4.420         |
| X4         | 5.610         |
| Y          | 1.270         |
| Y1         | 0.600         |
| Y2         | 1.020         |
| Y3         | 0.295         |
| Y4         | 1.825         |
| Y5         | 3.810         |
| Y6         | 0.180         |
| Y7         | 6.610         |

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